

# YJ Planar Schottky Barrier Diode Die Specification

150V 1A, 32mil, Schottky barrier diode die based on silicon planar process  
Part No.: PSB032H150SS-280A

## Main Products Characteristics

### Maximum Ratings

### Static Electrical Characteristics (Ta = 25°C)

$I_F = 1 \text{ A}$

2%

### Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 \* : Also can offer device with 8 mils thickness

2 \*\*: Cutting street width is around 1.5 mils

### Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after assembly.

Store in original container, in dessicated nitrogen, with no contamination.

Rating pa MICIDMICID 25Ang (x-none)BDC 2916 71f1tID 25reWhBTF3 6.72 Tf1 0 0 1 0 1m3 6.7 0 0 bce th noblyno